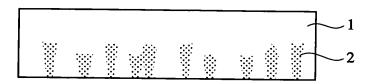
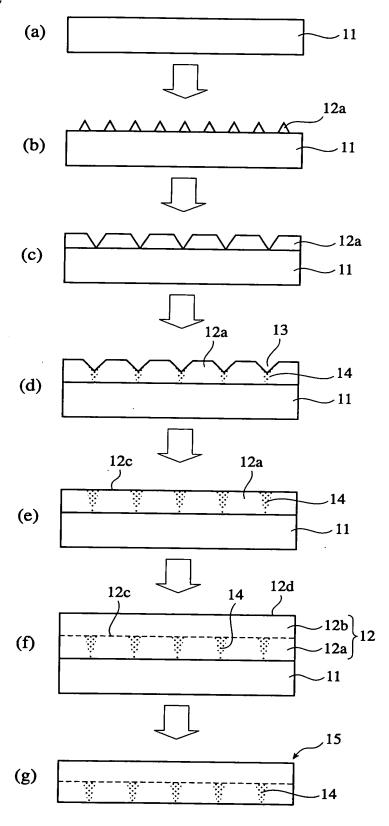
Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD
Filed: March 31, 2004
SUGHRUE Reference No. Q80822
Sheet 1 of 9

Fig. 1



Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD
Filed: March 31, 2004
SUGHRUE Reference No. Q80822
Sheet 2 of 9

Fig. 2



Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD
Filed: March 31, 2004
SUGHRUE Reference No. Q80822
Sheet 3 of 9

Fig. 3

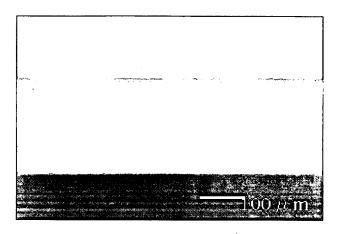
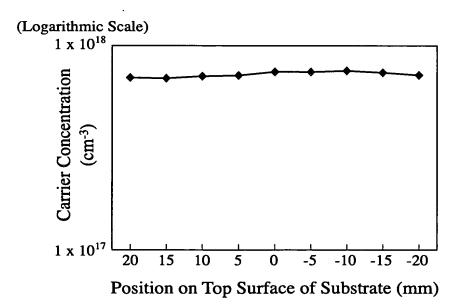


Fig. 4



Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD
Filed: March 31, 2004
SUGHRUE Reference No. Q80822
Sheet 4 of 9

Fig. 5

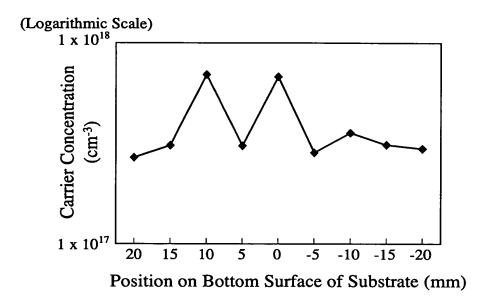
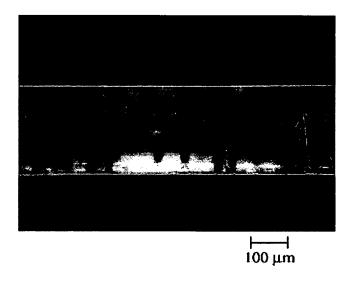
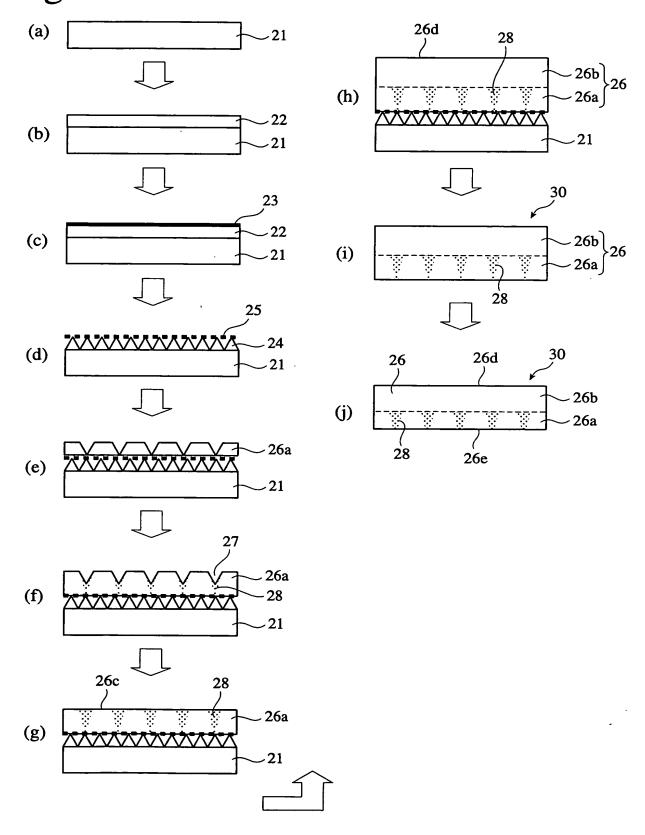


Fig. 6



Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD
Filed: March 31, 2004
SUGHRUE Reference No. Q80822
Sheet 5 of 9



Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD Filed: March 31, 2004 SUGHRUE Reference No. Q80822 Sheet 6 of 9

36b

36a

-31

-36b

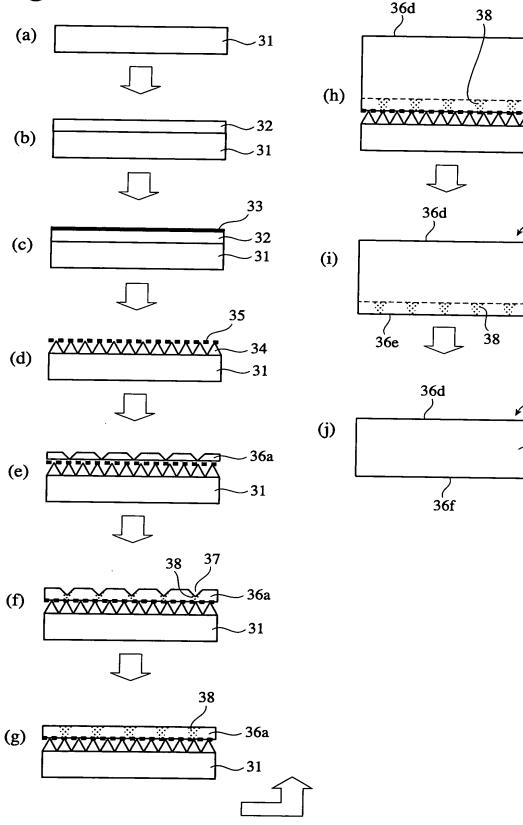
40

40'

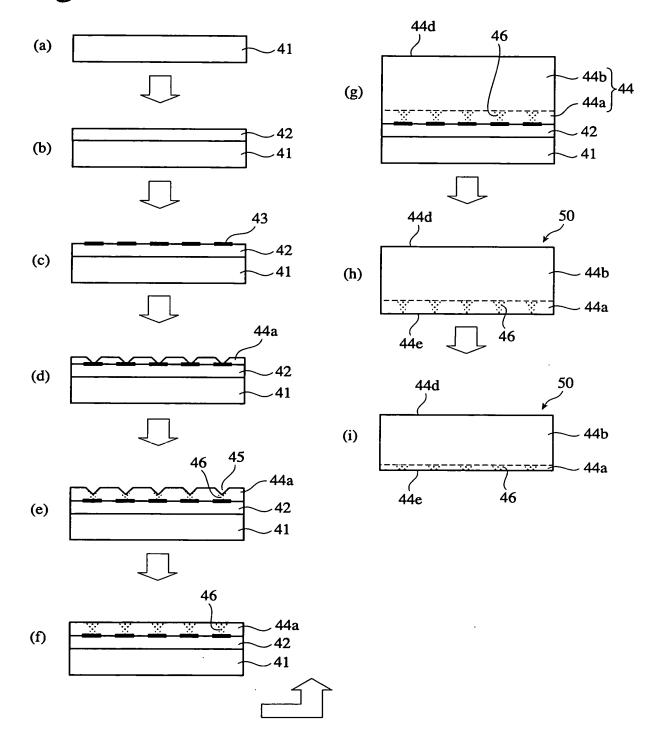
-36b

38

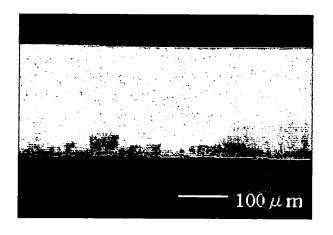
36



Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD
Filed: March 31, 2004
SUGHRUE Reference No. Q80822
Sheet 7 of 9



Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD
Filed: March 31, 2004
SUGHRUE Reference No. Q80822
Sheet 8 of 9



Masatomo SHIBATA
III-V NITRIDE SEMICONDUCTOR SUBSTRATE
AND ITS PRODUCTION METHOD
Filed: March 31, 2004
SUGHRUE Reference No. Q80822
Sheet of 9

